

Single 8-Ch/Differential 4-Ch Latchable Analog Multiplexers

DESCRIPTION

The DG428, DG429 analog multiplexers have on-chip address and control latches to simplify design in microprocessor based applications. Break-before-make switching action protects against momentary crosstalk of adjacent input signals.

The DG428 selects one of eight single-ended inputs to a common output, while the DG429 selects one of four differential inputs to a common differential output.

An on channel conducts current equally well in both directions. In the off state each channel blocks voltages up to the power supply rails. An enable (EN) function allows the user to reset the multiplexer/demultiplexer to all switches off for stacking several devices. All control inputs, address (A_x) and enable (EN) are TTL compatible over the full specified operating temperature range.

The silicon-gate CMOS process enables operation over a wide range of supply voltages. The absolute maximum voltage rating is extended to 44 V. Additionally, single supply operation is also allowed and an epitaxial layer prevents latchup.

On-board TTL-compatible address latches simplify the digital interface design and reduce board space in bus-controlled systems such as data acquisition systems, process controls, avionics, and ATE.

FEATURES

- Halogen-free according to IEC 61249-2-21 **Definition**
- Low $R_{DS(on)}$: 55 Ω
- Low Charge Injection: 1 pC
- On-Board TTL Compatible Address Latches
- High Speed t_{TRANS}: 160 ns
- Break-Before-Make
- Low Power Consumption: 0.3 mW
- Compliant to RoHS Directive 2002/95/EC

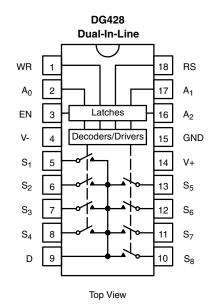
BENEFITS

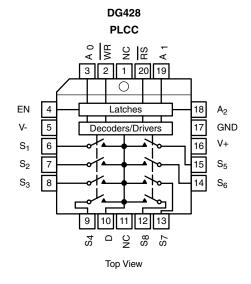
- · Improved System Accuracy
- Microprocessor Bus Compatible
- Easily Interfaced
- Reduced Crosstalk
- High Throughput
- Improved Reliability

APPLICATIONS

- · Data Acquisition Systems
- **Automatic Test Equipment**
- Avionics and Military Systems
- Communication Systems
- Microprocessor-Controlled Analog Systems
- Medical Instrumentation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



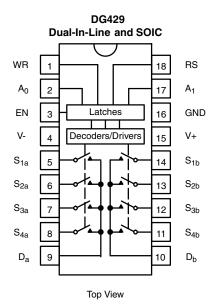


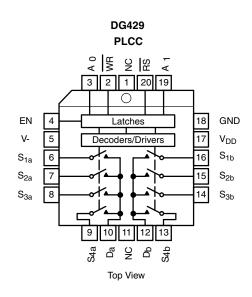


HALOGEN FREE



FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRU	TRUTH TABLE - DG428							
	8	-Chanr	nel Sing	le-End	ed Mult	iplexer		
A ₂	A ₁	A ₀	EN	WR	RS	On Switch		
Latch	Latching							
Х	Х	Х	Х	<u>_</u>	1	Maintains previous switch condition		
Reset								
Х	Х	Х	Х	Х	0	None (latches cleared)		
Trans	parent	Operati	ion					
Х	Χ	Χ	0	0	1	None		
0	0	0	1	0	1	1		
0	0	1	1	0	1	2		
0	1	0	1	0	1	3		
0	1	1	1	0	1	4		
1	0	0	1	0	1	5		
1	0	1	1	0	1	6		
1	1	0	1	0	1	7		
1	1	1	1	0	1	8		

TRU	TRUTH TABLE - DG429									
	Differential 4-Channel Multiplexer									
A ₁	A ₀	EN	WR	RS	On Switch					
Latchii	Latching									
Х	X X X Maintains previous switch condition									
Reset										
Х	х	Х	Х	0	None (latches cleared)					
Transp	arent Op	peration								
Х	Х	0	0	1	None					
0	0	1	0	1	1					
0	1	1	0	1	2					
1	0	1	0	1	3					
1	1	1	0	1	4					

Logic "0" = $V_{AL} \le 0.8 \text{ V}$ Logic "1" = $V_{AH} \ge 2.4 \text{ V}$ X = Don't Care

ORDERING INFORMATION - DG428							
Temp Range Package Part Number							
	18-pin Plastic DIP	DG428DJ					
- 40 °C to 85 °C	16-pili Flastic DIF	DG428DJ-E3					
- 40 C to 65 C	20-pin PLCC	DG428DN					
	20-pill PLCC	DG428DN-E3					

ORDERING INFORMATION - DG429							
Temp Range	Package	Part Number					
	18-pin Plastic DIP	DG429DJ					
	10-piii Flasiic DiF	DG429DJ-E3					
- 40 °C to 85 °C	20-pin PLCC	DG429DN					
- 40 C to 65 C	20-piii FLOO	DG429DN-E3					
	18-pin Widebody SOIC	DG429DW					
	10-pili widebody 5010	DG429DW-E3					



	Parameter	Symbol	Limit	Unit
	V+	,	44	
Voltages Referenced to V-	GND		25	
Digital Inputs ^a , V _S , V _D			(V-) - 2 V to (V+) + 2 V or 30 mA, whichever occurs first	V
Current (Any Terminal)			30	mA
Peak Current, S or D (Pulsed at 1 ms, 10 % Duty Cycle Max)			100	
Ctorogo Tomporoturo	(AK Suffix)		- 65 to 150	°C
Storage Temperature	(DJ, DN Suffix)		- 65 to 125	C
	18-pin Plastic DIP ^c		470	
Power Dissipation (Package) ^b	18-pin CerDIP ^d		900	mW
	20-pin PLCC ^f		800	IIIVV
	28-Pin Widebody SOIC ^f		450	

Notes:

- a. Signals on S_X , D_X or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads soldered or welded to PC board.
- c. Derate 6.3 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.
- e. Derate 10 mW/°C above 75 °C.
- f. Derate 6 mW/°C above 75 °C.



SPECIFICATIONS ^a		Test Condition Unless Otherwise S				A Suffix - 55 °C to 125 °C		_	uffix to 85 °C	
		V+ = 15 V, V- = - 15 V,	$\overline{WR} = 0,$							1
Parameter	Symbol	$\overline{RS} = 2.4 \text{ V}, \text{ V}_{IN} = 2.4$	V, 0.8 V ^f	Temp.b	Typ.c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch										
Analog Signal Range ^e	V _{ANALOG}			Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	R _{DS(on)}	$V_D = \pm 10 \text{ V}, V_{AL} = I_S = -1 \text{ mA}, V_{AH} = -1 \text{ mA}$		Room Full	55		100 125		100 125	Ω
Greatest Change in R _{DS(on)} Between Channels ^g	$\Delta R_{DS(on)}$	- 10 V < V _S < 10 I _S = - 1 mA) V	Room	5					%
Source Off Leakage Current	I _{S(off)}	$V_S = \pm 10 \text{ V},$ $V_{EN} = 0 \text{ V}, V_D = \pm$		Room Full	± 0.03	- 0.5 - 50	0.5 50	- 0.5 - 50	0.5 50	
Drain Off Leakage Current	1	$V_{EN} = 0 \text{ V}$ $V_{D} = \pm 10 \text{ V}$	DG428	Room Full	± 0.07	- 1 - 100	1 100	- 1 - 100	1 100	=
Drain Off Leakage Current	I _{D(off)}	$V_{S} = \pm 10 \text{ V}$	DG429	Room Full	± 0.05	- 1 - 50	1 50	- 1 - 50	1 50	nA
Drain On Leakage Current	ln()	$V_S = V_D = \pm 10 \text{ V}$ $V_{EN} = 2.4 \text{ V}$	DG428	Room Full	± 0.07	- 1 - 100	1 100	- 1 - 100	1 100	
Diam on Leakage ounem	I _{D(on)}	$V_{AL} = 0.8 \text{ V}$ $V_{AH} = 2.4 \text{ V}$	DG429	Room Full	± 0.05	- 1 - 50	1 50	- 1 - 50	1 50	
Digital Control										
Logic Input Current	I _{AH}	$V_A = 2.4 \text{ V}$		Full	0.01		1		1	
Input Voltage High	'AH	V _A = 15 V		Full	0.01		1		1	μΑ
Logic Input Current Input Voltage Low	I _{AL}	$V_{EN} = 0 \text{ V, } 2.4 \text{ V, } V_{A}$ $\overline{RS} = 0 \text{ V, } \overline{WR} = 0$		Full	- 0.01	- 1		- 1		μπ
Logic Input Capacitance	C _{in}	f = 1 MHz		Room	8					pF
Dynamic Characteristics										
Transition Time	t _{TRANS}	See Figure 5		Room Full	150		250 300		250 300	
Break-Before-Make Interval	t _{OPEN}	See Figure 4		Full	30	10		10		
Enable and Write Turn-On Time	t _{ON(EN,WR)}	See Figure 6 an	d 7	Room Full	90		150 225		150 225	ns
Enable and Reset Turn-Off Time	t _{OFF(EN,RS)}	See Figure 6 an		Room Full	55		150 300		150 300	
Charge Injection	Q	$V_{GEN} = 0 \text{ V, R}_{GEN}$ $C_L = 1 \text{ nF, See Fig}$	jure 9	Room	1					рC
Off Isolation	OIRR	$V_{EN} = 0 \text{ V, } R_L = 3$ $C_L = 15 \text{ pF, } V_S = 7$ $f = 100 \text{ kHz}$	V _{RMS}	Room	- 75					dB
Source Off Capacitance	C _{S(off)}	$V_S = 0 \text{ V}, V_{EN} = 0 \text{ V}, f$	= 1 MHz	Room	11					
Drain Off Capacitance	C _{D(off)}	V _D = 0 V	DG428 DG429	Room Room	40 20					pF
Drain On Capacitance	C _{D(on)}	V _{EN} = 0 V f = 1 MHz	DG428	Room	54					pi
Minimum Input Timing Requiren	nente		DG429	Room	34		<u> </u>		<u> </u>	<u> </u>
Write Pulse Width	t _W			Full		100		100		
A _X , EN Data Set Up time	t _S	See Figure 2		Full		100		100	-	-
A _X , EN Data Set Op time	t _H	Jee Figure 2		Full		100		100	-	ns
Reset Pulse Width		V _S = 5 V, See Fig	ure 3	Full		100		100	-	1
Power Supplies	t _{RS}	VS - 5 V, 566 Fig	4.00	Luli		100		100		
Positive Supply Current	I+			Room	20		100	<u> </u>	100	l
	i +	$V_{EN} = V_A = 0$, $\overline{RS} = 5 \text{ V}$		1100111	20		100	l	100	μΑ



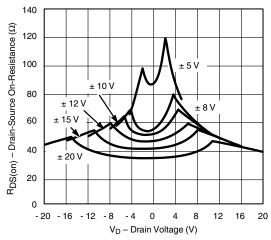
		ply) Test Condition Unless Otherwise S	pecified				uffix o 125 °C		uffix to 85 °C	
Parameter	Symbol	$V+ = 12 \text{ V}, V- = 0 \text{ V}, \overline{\text{V}}$ $\overline{\text{RS}} = 2.4 \text{ V}, V_{\text{IN}} = 2.4$		Temp.b	Typ.c	Min.d	Max. ^d	Min.d	Max. ^d	Unit
Analog Switch	Oymboi		-,	Temp.	Typ.	141111.	wax.	141111.	wax.	Oilit
Analog Signal Range ^e	V _{ANALOG}			Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	$V_D = \pm 10 \text{ V}, V_{AL} = 0.8 \text{ V}$ $I_S = -500 \mu A, V_{AH} = 2.4 \text{ V}$		Room	80		150	-	150	Ω
R _{DS(on)} Match ^g	$\Delta R_{DS(on)}$	$0 \text{ V} < \text{V}_{\text{S}} < 10$ $\text{I}_{\text{S}} = -1 \text{ mA}$	V	Room	5					%
Source Off Leakage Current	I _{S(off)}	$V_S = 0 \text{ V}, 10 \text{ V}$ $V_{EN} = 0 \text{ V}, V_D = 10$	′, V, 0 V	Room Full	± 0.03	- 0.5 - 50	0.5 50	- 0.5 - 50	0.5 50	
Drain Off Leakage Current	I _{D(off)}	V _D = 0 V, 10 V V _S = 10 V, 0 V	DG428	Room Full	± 0.07	- 1 - 100	1 100	- 1 - 100	1 100	
Diam on Loakago ourione	·D(011)	$V_{EN} = 0 V$	DG429	Room Full	± 0.05	- 1 - 50	1 50	- 1 - 50	1 50	nA
D : 0 1 1 0		$V_S = V_D = 0 \text{ V}, 10 \text{ V}$ $V_{EN} = 2.4 \text{ V}$	DG428	Room Full	± 0.07	- 1 - 100	1 100	- 1 - 100	1 100	
Drain On Leakage Current	I _{D(on)}	$V_{AL} = 0.8 \text{ V}$ $V_{AH} = 2.4 \text{ V}$	DG429	Room Full	± 0.05	- 1 - 50	1 50	- 1 - 50	1 50	
Digital Control	<u> </u>			I.			ı			
Logic Input Current	I _{AH}	$V_A = 2.4 \text{ V}$		Full			1		1	
Input Voltage High	'AH	V _A = 12 V		Full			1		1	μΑ
Logic Input Current Input Voltage Low	I _{AL}	$V_{EN} = 0 \text{ V, } 2.4 \text{ V, } V_{A}$ RS = 0 V, WR =	(= 0 V	Full		- 1		- 1		'
Dynamic Characteristics										
Transition Time	t _{TRANS}	$S_1 = 10 \text{ V/ } 2 \text{ V, } S_8 = 2 \text{ See Figure 5}$! V/ 10 V	Room Full	160		280 350		280 350	
Break-Before-Make Interval	t _{OPEN}	See Figure 4		Room Full	40	25 10		25 10		ns
Enable and WriteTurn-On Time	t _{ON(EN,WR)}	S ₁ = 5 V See Figure 6 an	d 7	Room Full	110		300 400		300 400	115
Enable and Reset Turn-Off Time	t _{OFF(EN,RS)}	$S_1 = 5 \text{ V}$ See Figure 6 an	d 8	Room Full	70		300 400		300 400	
Charge Injection	Q	$V_{GEN} = 6 \text{ V, R}_{GEN} = 0 \text{ V, R}_{GEN} = 0 \text{ N}$ $C_L = 1 \text{ nF, See Fig}$	= 0 Ω ure 9	Room	4					рС
Off Isolation	OIRR	$V_{EN} = 0 \text{ V, } R_{L} = 300 \Omega$ $C_{L} = 15 \text{ pF, } V_{S} = 7 V_{RMS}$ $f = 100 \text{ kHz}$		Room	- 75					dB
Minimum Input Timing Requiren	nents									
Write Pulse Width	t _W			Full		100		100		
A _X , EN Data Set Up time	t _S	See Figure 2		Full		100		100		ns
A _X , EN Data Hold Time	t _H			Full		10		10		113
Reset Pulse Width	t _{RS}	V _S = 5 V, See Fig	ure 3	Full		100		100		
Power Supplies										
Positive Supply Current	l+	$V_{EN} = 0 \text{ V}, V_A = 0, \overline{R}$	S = 5 V	Room	20		100		100	μΑ

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

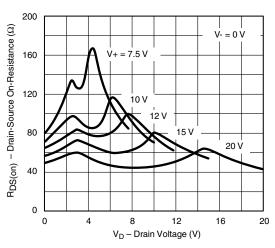
g.
$$\Delta R_{DS(on)} = \left(\frac{R_{DS(on)} MAX - R_{DS(on)} MIN}{R_{DS(on)} AVE}\right) \times 100 \%$$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

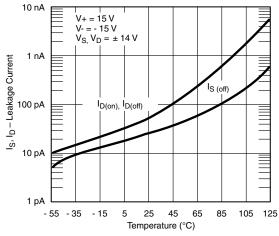
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



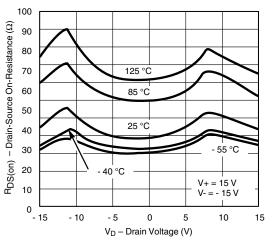
 $R_{DS(on)}$ vs. V_D and Supply Voltage



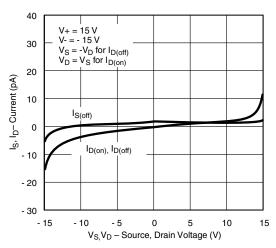
Single Supply $R_{DS(on)}\, vs. \,\, V_D$ and Supply



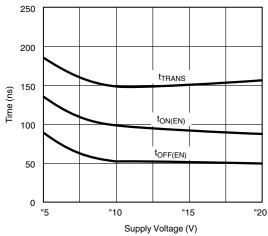
I_D , I_S Leakages vs. Temperature



 $R_{DS(on)}$ vs. V_D and Temperature



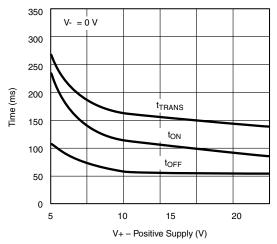
 ${\sf I}_{\sf D}$, ${\sf I}_{\sf S}$ Leakage Currents vs. Analog Voltage



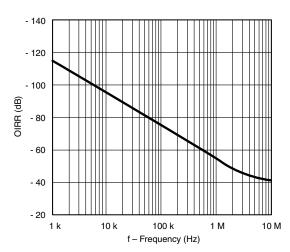
Switching Times vs. Power Supply Voltage



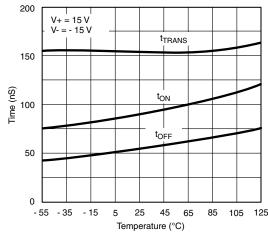
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



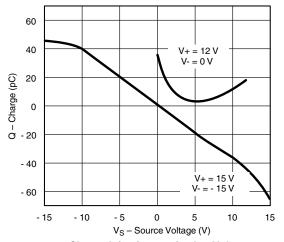
Switching Times vs. Single Supply



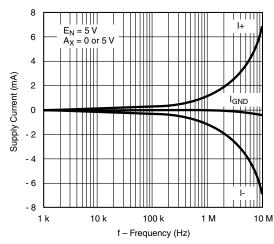
Off-Isolation vs. Frequency



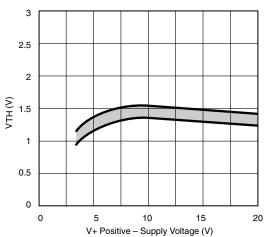
Switching Times vs. Temperature



Charge Injection vs. Analog Voltage

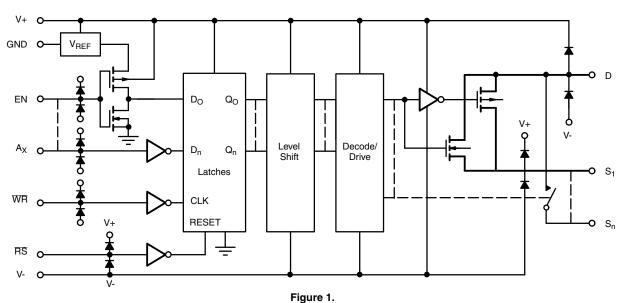


Supply Currents vs. Switching Frequency



Input Switching Threshold vs. Positive Supply Voltage

SCHEMATIC DIAGRAM (Typical Channel)



TIMING DIAGRAMS

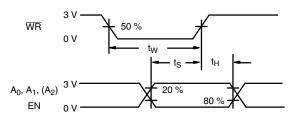


Figure 2.

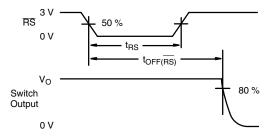


Figure 3.

TEST CIRCUITS

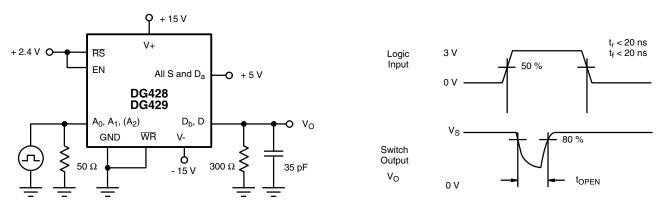


Figure 4. Break-Before-Make



TEST CIRCUITS

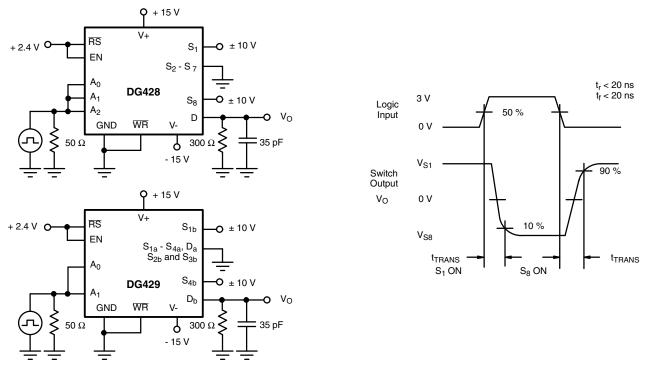


Figure 5. Transition Time

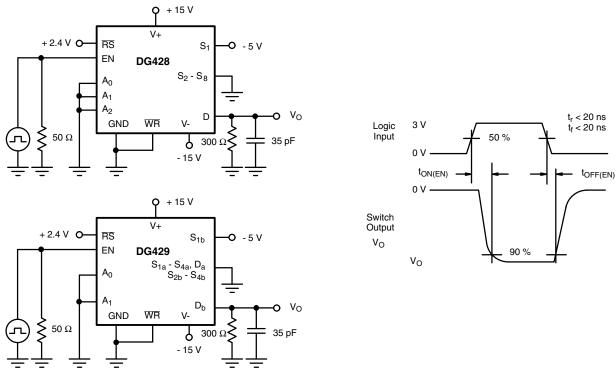


Figure 6. Enable t_{ON}/t_{OFF} Time

TEST CIRCUITS

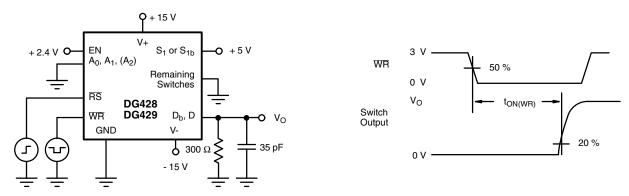


Figure 7. Write Turn-On Time t_{ON(WR)}

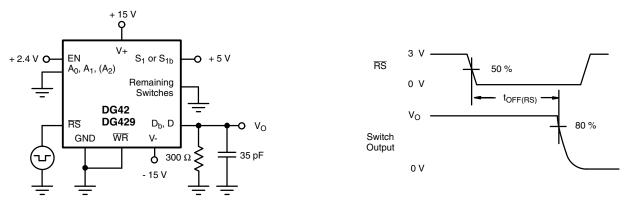
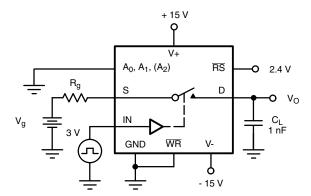
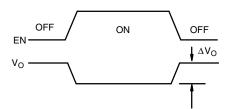


Figure 8. Reset Turn-Off Time toFF(RS)







 ΔV_O is the measured voltage error due to charge injection. The charge in coulombs is Q = $C_L x \Delta V_O$



DETAILED DESCRIPTION

The internal structure of the DG428, DG429 includes a 5 V logic interface with input protection circuitry followed by a latch, level shifter, decoder and finally the switch constructed with parallel n- and p-channel MOSFETs (see Figure 1).

The input protection on the logic lines A₀, A₁, A₂, EN and control lines WR, RS shown in Figure 1 minimizes susceptibility to ESD that may be encountered during handling and operational transients.

The logic interface is a CMOS logic input with its supply voltage from an internal + 5 V reference voltage. The output of the input inverter feeds the data input of a D type latch. The level sensitive D latch continuously places the D_X input signal on the Q_X output when the \overline{WR} input is low, resulting in transparent latch operation. As soon as WR returns high the latch holds the data last present on the D_n input, subject to the "Minimum Input Timing Requirements" table.

Following the latches the Q_n signals are level shifted and decoded to provide proper drive levels for the CMOS switches. This level shifting ensures full on/off switch operation for any analog signal level between the V+ and V- supply rails.

The EN pin is used to enable the address latches during the WR pulse. It can be hard wired to the logic supply or to V+ if one of the channels will always be used (except during a reset) or it can be tied to address decoding circuitry for memory mapped operation. The RS pin is used as a master reset. All latches are cleared regardless of the state of any other latch or control line. The WR pin is used to transfer the state of the address control lines to their latches, except during a reset or when EN is low (see Truth Tables).

APPLICATIONS HINTS

Bus Interfacing

The DG428, DG429 minimize the amount of interface hardware between a microprocessor system bus and the analog system being controlled or measured. The internal TTL compatible latches give these multiplexers write-only memory, that is, they can be programmed to stay in a particular switch state (e.g., switch 1 on) until the microprocessor determines it is necessary to turn different switches on or turn all switches off (see Figure 10).

The input latches become transparent when WR is held low: therefore, these multiplexers operate by direct command of the coded switch state on $A_2,\,A_1,\,A_0.$ In this mode the DG428 is identical to the popular DG408. The same is true of the DG429 versus the popular DG409.

During system power-up, RS would be low, maintaining all eight switches in the off state. After RS returned high the DG428 maintains all switches in the off state.

When the system program performs a write operation to the address assigned to the DG428, the address decoder provides a $\overline{\text{CS}}$ active low signal which is gated with the WRITE (WR) control signal. At this time the data on the DATA BUS (that will determine which switch to close) is stabilizing. When the WR signal returns to the high state, (positive edge) the input latches of the DG428 save the data from the DATA BUS. The coded information in the A_0 , A_1 , A_2 and EN latches is decoded and the appropriate switch is turned on.

The EN latch allows all switches to be turned off under program control. This becomes useful when two or more DG428s are cascaded to build 16-line and larger multiplexers.

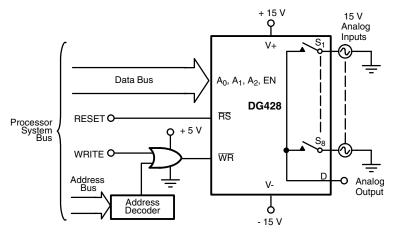
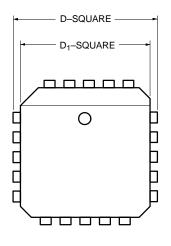


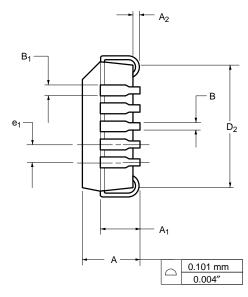
Figure 10. Bus Interface

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishav.com/ppg?70063.



PLCC: 20-LEAD



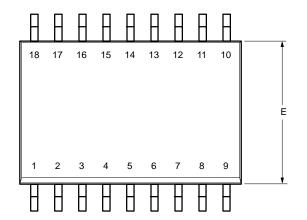


	MILLIN	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	4.20	4.57	0.165	0.180		
A ₁	2.29	3.04	0.090	0.120		
A ₂	0.51	-	0.020	-		
В	0.331	0.553	0.013	0.021		
B ₁	0.661	0.812	0.026	0.032		
D	9.78	10.03	0.385	0.395		
D ₁	8.890	9.042	0.350	0.356		
D ₂	7.37	8.38	0.290	0.330		
e ₁	1.27 BSC 0.050 BSC					
ECN: S-03946—Rev. C, 09-Jul-01 DWG: 5306						

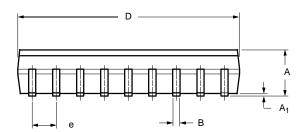
www.vishay.com Document Number: 71263

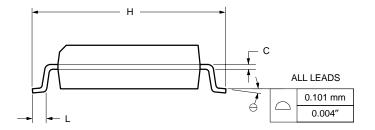


SOIC (WIDE-BODY): 18-LEAD



	MILLIM	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	2.15	2.90	0.085	0.114		
A ₁	0.10	0.30	0.004	0.012		
В	0.35	0.45	0.014	0.018		
С	0.23	0.28	0.009	0.011		
D	11.25	12.45	0.443	0.490		
Е	7.25	8.00	0.285	0.315		
е	1.27	BSC	0.050	BSC		
Н	9.80	10.60	0.386	0.417		
L	0.60	1.00	0.024	0.039		
\ominus	0°	8°	0°	8°		
ECN: S-03946—Rev. C, 09-Jul-01 DWG: 5302						







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